



MOS FET
FC8J33040L

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Dual N-channel MOSFET

For switching
For DC-DC Converter

■ Features

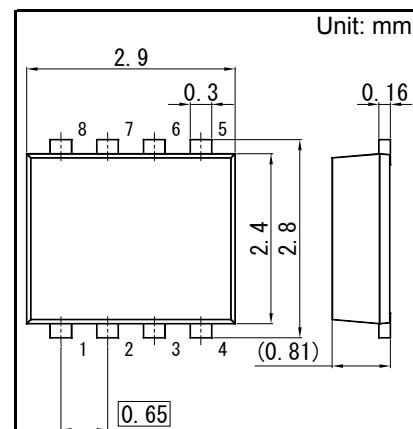
- Low drain-source On-state Resistance :
RDS(on) typ = 48 mΩ (VGS = 4.5 V)
- High-speed switching : Qg = 2.8 nC
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: 7A

■ Basic Part Number : Dual Nch MOS 33V (Individual)

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)



1. Tr.1 Source	5. Tr.2 Drain
2. Tr.1 Gate	6. Tr.2 Drain
3. Tr.2 Source	7. Tr.1 Drain
4. Tr.2 Gate	8. Tr.1 Drain

Panasonic	WMini8-F1
JEITA	SC-115
Code	—

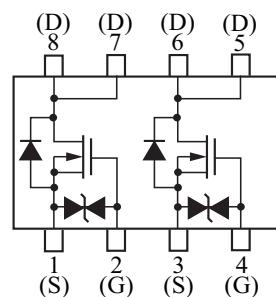
■ Absolute Maximum Ratings Ta = 25 °C Tr.1, Tr.2

Parameter	Symbol	Rating	Unit
Drain-source Voltage	VDS	33	V
Gate-source Voltage	VGS	±20	V
Drain Current (Steady State) ^{*1}	ID	5	
Drain Current (t = 10 s) ^{*1}		5.5	
Drain Current (Pulsed) ^{*1,*2}	IDp	20	
Source Current (Pulsed) (Body Diode) ^{*1,*2}	ISp (BD)	5	A
Total Power Dissipation (Steady State) ^{*1}	PD	1	W
Total Power Dissipation (t = 10 s) ^{*1}		1.3	
Channel Temperature	Tch	150	°C
Operating Ambient Temperature	Topr	-40 to + 85	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Note) *1 Device mounted on a glass-epoxy board (See Figure 1)

*2 Pulse test: Ensure that the channel temperature does not exceed 150°C.

Internal Connection



Pin Name

1. Tr.1 Source	5. Tr.2 Drain
2. Tr.1 Gate	6. Tr.2 Drain
3. Tr.2 Source	7. Tr.1 Drain
4. Tr.2 Gate	8. Tr.1 Drain

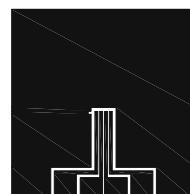


Figure1 FR4 Glass-Epoxy Board
25.4 mm × 25.4 mm × 0.8 mm



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$ Tr.1, Tr.2

Static Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	33			V
Zero Gate Voltage Drain Current	IDSS	VDS = 33 V, VGS = 0 V			1	μA
Gate-source Leakage Current	IGSS	VGS = ± 16 V, VDS = 0 V			± 10	μA
Gate-source Threshold Voltage	Vth	ID = 0.26 mA, VDS = 10 V	1		2.5	V
Drain-source On-state Resistance ^{*1}	RDS(on)1	ID = 2.5 A, VGS = 10 V		32	38	$\text{m}\Omega$
	RDS(on)2	ID = 2.5 A, VGS = 4.5 V		48	68	

Dynamic Characteristics

Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V $f = 1 \text{ MHz}$	220		pF
Output Capacitance	Coss		40		
Reverse Transfer Capacitance	Crss		35		
Turn-on Delay Time ^{*2}	td(on)	VDD = 15 V, VGS = 0 to 10 V ID = 2.5 A	7		ns
Rise Time ^{*2}	tr		3		
Turn-off Delay Time ^{*2}	td(off)		15		
Fall Time ^{*2}	tf	ID = 2.5 A	9		
Total Gate Charge	Qg	VDD = 15 V, VGS = 0 to 4.5 V, ID = 5 A	2.8		nC
Gate-source Charge	Qgs		1.1		
Gate-drain Charge	Qgd		1.2		

Body Diode Characteristic

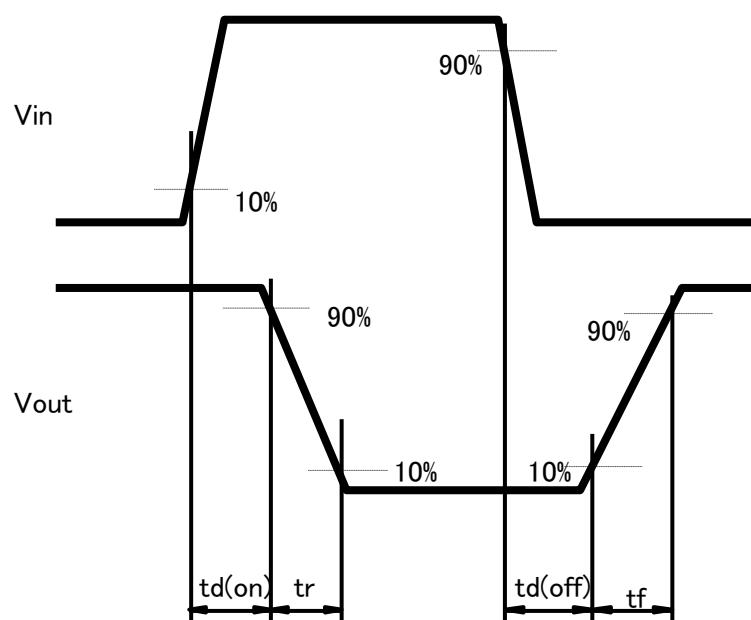
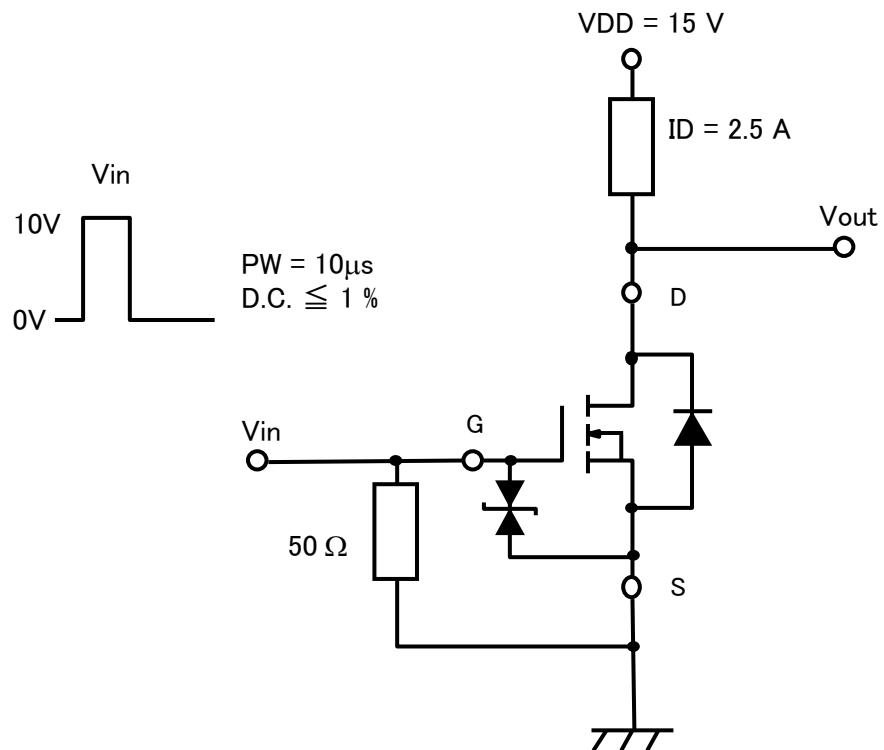
Diode Forward Voltage ^{*1}	VSD	IS = 2.5 A, VGS = 0 V		0.8	1.2	V
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Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

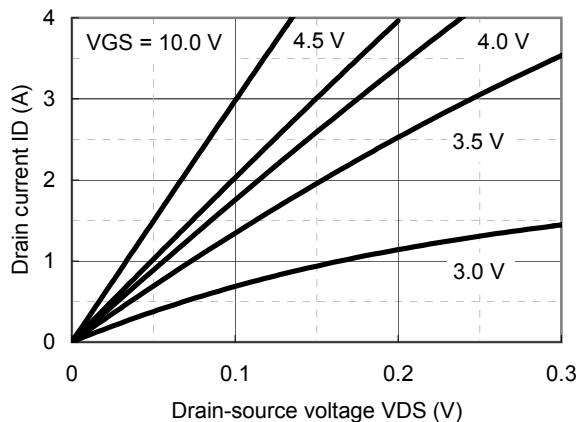
2. *1 Pulse test: Ensure that the channel temperature does not exceed 150°C .

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

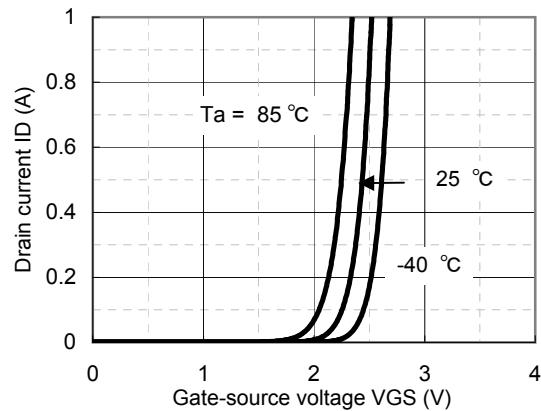
*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



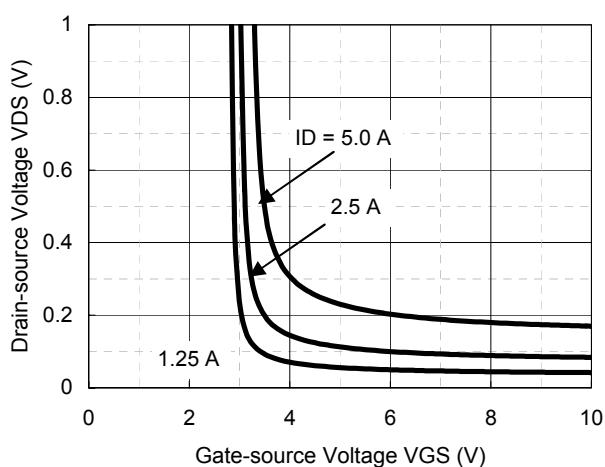
ID - VDS



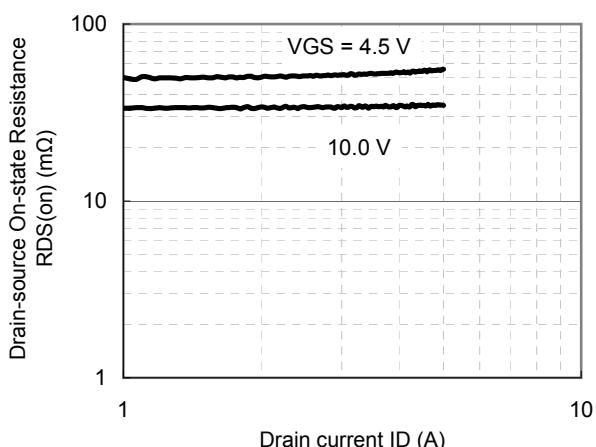
ID - VGS



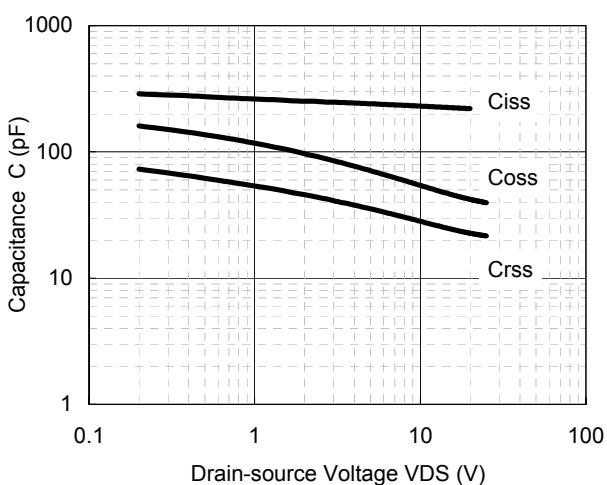
VDS - VGS



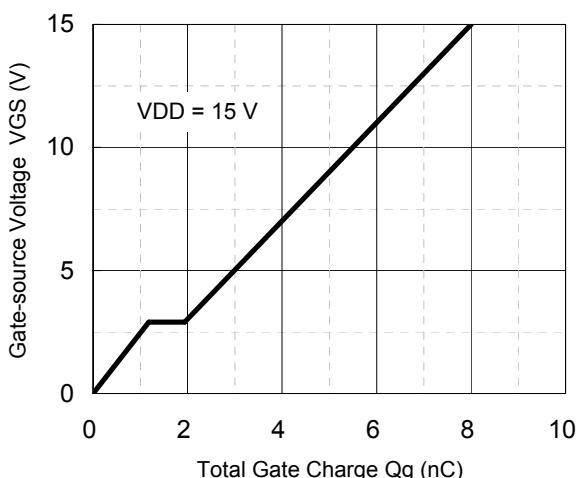
RDS(on) - ID



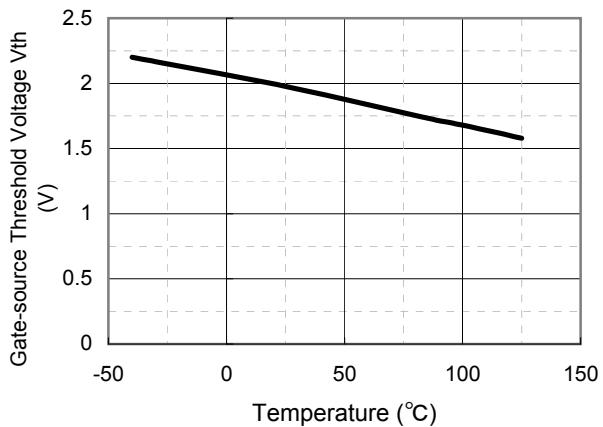
Capacitance - VDS



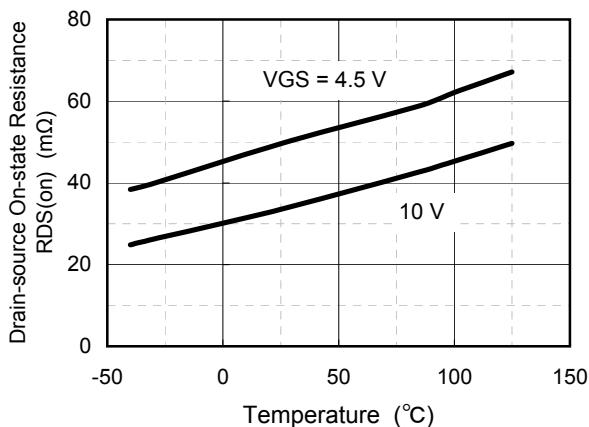
Dynamic Input/Output Characteristics



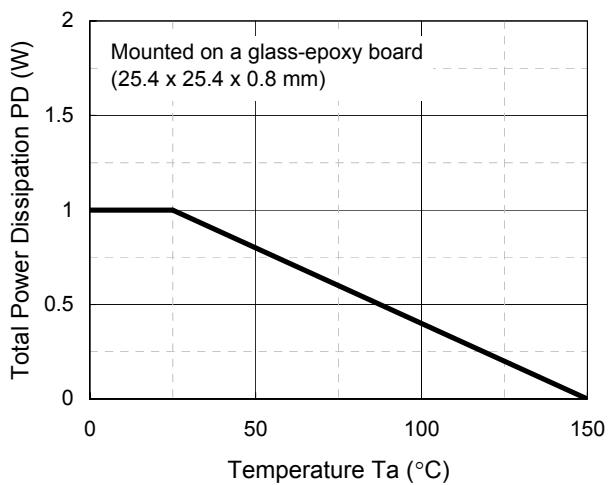
V_{th} - T_a



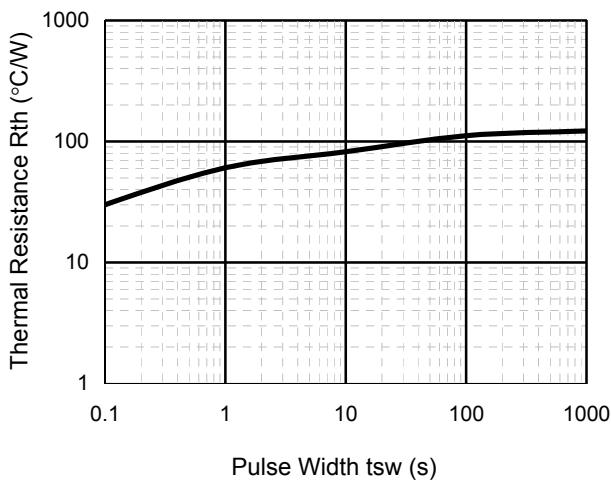
RDS(on) - T_a



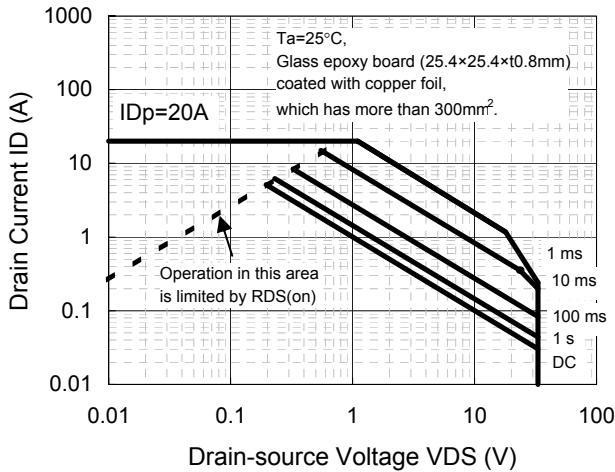
PD - T_a



R_{th} - t_{sw}



Safe Operating Area

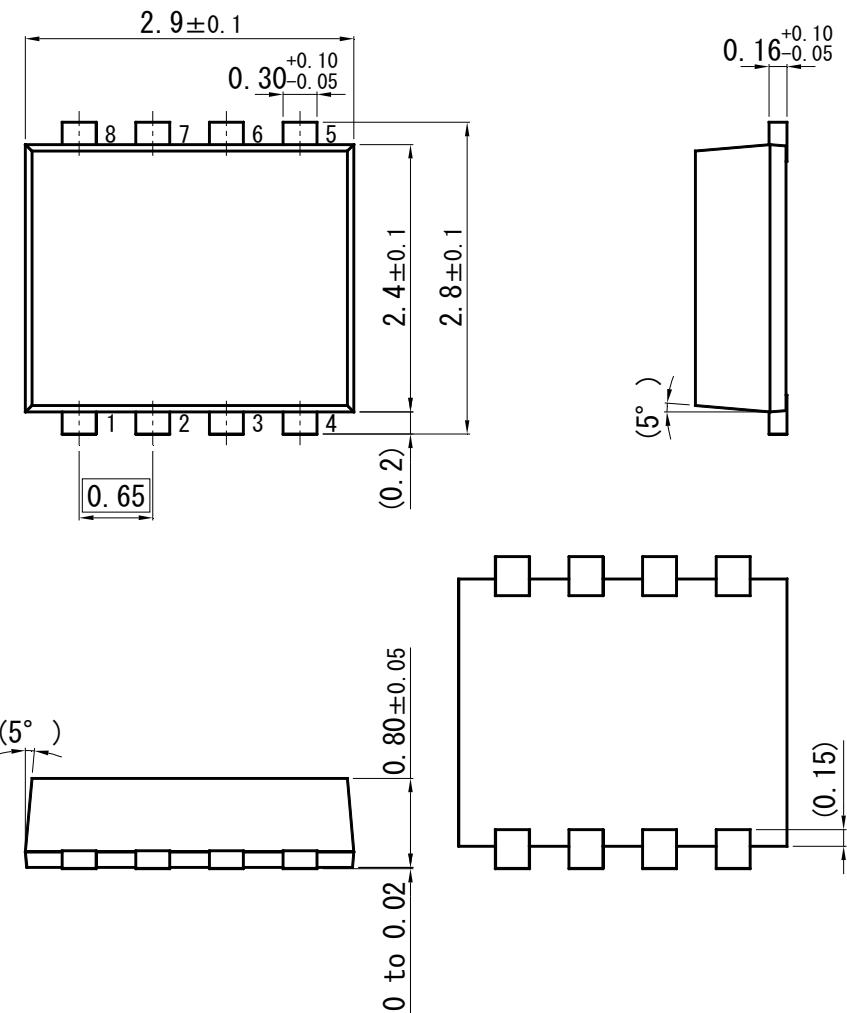


Panasonic

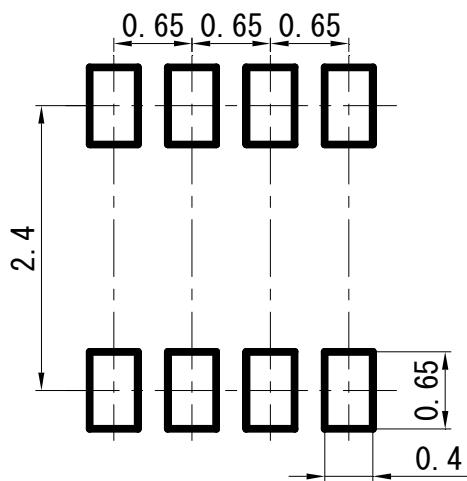
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WMini8-F1

Unit : mm



■ Land Pattern (Reference) (Unit : mm)



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